

IN THE SPECIFICATION

Please replace the paragraph beginning on page 5, line 17, with the following paragraph:

A nonvolatile semiconductor memory device according to an aspect of the invention comprises: a semiconductor substrate having a peripheral circuit region and a memory cell region; a plurality of erasable and programmable memory cell transistors each having a gate electrode and provided in the memory cell region; a plurality of peripheral transistors each having a gate electrode and provided in the peripheral circuit region; first post-oxidation films each provided on the gate electrode of all of the plurality of erasable and programmable memory cell transistors; second post-oxidation films each provided on the gate electrode of all of the plurality of peripheral transistors; first insulating films each provided on the first post-oxidation films and covering a side surface of the gate electrode of all of the plurality of erasable and programmable memory cell transistors, the first insulating films being harder for an oxidizing agent to pass therethrough than a silicon oxide film, and the first insulating films being oxidized; and second insulating films each provided on the second post-oxidation films and covering a side surface of the gate electrode of all of the peripheral transistors, the second insulating films being harder for an oxidizing agent to pass therethrough than a silicon oxide film, and the second insulating films being oxidized.

A nonvolatile semiconductor memory device comprises: a semiconductor substrate having a peripheral circuit region and a memory cell region; a plurality of erasable and programmable memory cell transistors each having a gate electrode and provided in the memory cell region; a selection transistor having a gate electrode and provided in the memory cell region; a peripheral transistor having a gate electrode and provided in the peripheral circuit region; first post-oxidation films each provided on the gate electrode of all

of the plurality of erasable and programmable memory cell transistors; a second post-oxidation film provided on the gate electrode of the selection transistor; a third post-oxidation film provided on the gate electrode of the peripheral transistor; and an insulating film covering the plurality of erasable and programmable memory cell transistors, the selection transistor, and the peripheral transistor, the insulating film being harder for an oxidizing agent to pass therethrough than a silicon oxide film, and the insulating film having an oxidized region, wherein the insulating film comprises a silicon nitride film, and the oxidized region is provided in a surface of the silicon nitride film.

**Please replace the Abstract paragraph beginning on page 38, line 2, with the following paragraph:**

~~A nonvolatile semiconductor memory device includes memory cell transistors, peripheral transistors, first post-oxidation films provided on the gate electrode of all of the memory cell transistors, second post-oxidation films provided on the gate electrode of all of the peripheral transistors, first insulating films provided on the first post-oxidation films and covering a side surface of the gate electrode of all of the memory cell transistors and second insulating films provided on the second post-oxidation films and covering a side surface of the gate electrode of all of the peripheral transistors. The first and second insulating films are harder for an oxidizing agent to pass therethrough than a silicon oxide film, and the first and second insulating films are oxidized.~~

A nonvolatile semiconductor memory device includes erasable and programmable memory cell transistors, a selection transistor, a peripheral transistor, first post-oxidation films each provided on a gate electrode of all of the plurality of erasable and programmable memory cell transistors, a second post-oxidation film provided on a gate electrode of the

selection transistor, a third post-oxidation film provided on a gate electrode of the peripheral transistor, and an insulating film covering the memory cell transistors, the selection transistor, and the peripheral transistor. The insulating film is harder for an oxidizing agent to pass through than a silicon oxide film. The insulating film has an oxidized region. The insulating film includes a silicon nitride film. The oxidized region is provided in a surface of the silicon nitride film.